

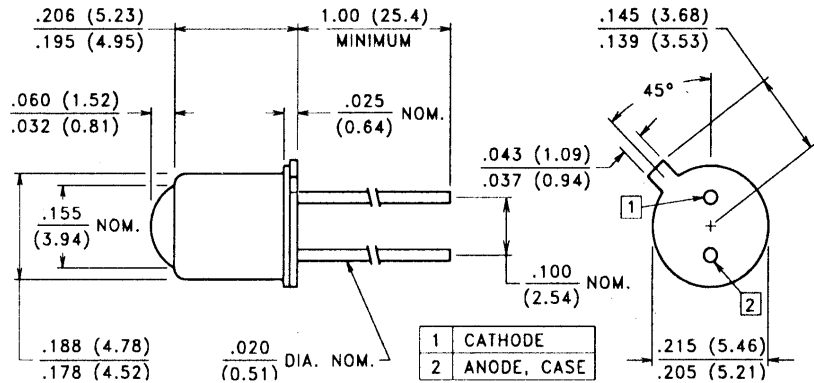
# GaAlAs Infrared Emitting Diodes

TO-46 Lensed Package — 880 nm

# VTE1163H



## PACKAGE DIMENSIONS inch (mm)



CASE 24 TO-46 HERMETIC (Lensed)  
CHIP SIZE: .018" x .018"

## DESCRIPTION

This narrow beam angle TO-46 hermetic emitter contains a large area, double wirebonded, GaAlAs, 880 nm, high efficiency IRED chip suitable for higher current pulse applications.

## RoHS Compliant



## ABSOLUTE MAXIMUM RATINGS @ 25°C (unless otherwise noted) ■

Maximum Temperatures									
Storage and Operating:	-55°C to 125°C	Maximum Reverse Voltage:	5.0V						
Continuous Power Dissipation:	200 mW	Maximum Reverse Current @ $V_R = 5V$ :	10 $\mu A$						
Derate above 30°C:	2.11 mW/°C	Peak Wavelength (Typical):	880 nm						
Maximum Continuous Current:	100 mA	Junction Capacitance @ 0V, 1 MHz (Typ.):	35 pF						
Derate above 30°C:	1.05 mA/°C	Response Time @ $I_F = 20 mA$							
Peak Forward Current, 10 $\mu s$ , 100 pps:	3A	Rise: 1.0 $\mu s$ Fall: 1.0 $\mu s$							
Temp. Coefficient of Power Output (Typ.):	-8%/°C	Lead Soldering Temperature:	260°C						
		(1.6 mm from case, 5 seconds max.)							

## ELECTRO-OPTICAL CHARACTERISTICS @ 25°C (See also GaAlAs curves, pages 108-110)

Part Number ■	Output						Forward Drop		Half Power Beam Angle	
	Irradiance		Radiant Intensity	Total Power	Test Current	$V_F$				
	$E_e$	Condition		$I_e$	$P_O$	$I_{FT}$	@ $I_{FT}$	$\theta_{1/2}$		
	mW/cm <sup>2</sup>	distance	Diameter	mW/sr	mW	mA	Volts			
	Min.	Typ.	mm	mm	Min.	Typ.	Typ.	Max.	Typ.	
VTE1163H	22	28	36	6.4	285	110	1.0	2.8	3.5	$\pm 10^\circ$

■ Refer to General Product Notes, page 2.